

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	136	drive same select same transfer same reset same pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:46
L2	1273	drive adj transistor same select select adj transistor same transfer same reset same pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:46
L3	88	drive adj transistor same select adj transistor same transfer same reset same pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:47
L4	84	drive adj transistor same select adj transistor same transfer adj transistor same reset adj transistor same pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 15:06
L5	44	4 and lee.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:50
L6	7	4 and lee.in. and ju-il	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:52
L7	20	4 and hynix	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 14:09
L8	3	4 and hynix and logic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 14:54

L9	3	4 and hynix and logic and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 14:10
L10	1	4 and hynix and logic and gate.cim.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 14:11
L11	15	4 and logic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 14:54
L13	16	drive adj transistor same select adj transistor same transfer adj transistor same reset adj transistor and pixel and logic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 15:07
L14	1	13 not 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 15:07
L15	136	drive adj transistor and select adj transistor and transfer adj transistor and reset adj transistor and pixel and logic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 15:08
L16	120	15 not 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 15:08
L17	1	(US-20010012225-\$).did.	US-PGPUB	OR	OFF	2005/12/15 15:36
L18	1	(US-20010012225-\$).did. and drive and follower	US-PGPUB	OR	OFF	2005/12/15 15:36
L19	47543	(etching etched etch) near3 (wet-etching hydrofluoric acid HF buffered adj oxide adj etchant BOE)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/15 15:40

L20	916	mask near (removing removal) with thinner sulfuric with plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/15 15:40
L21	85948	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/15 15:40
L22	108	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/15 15:40
L23	108	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 15:40
L24	88	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and logic and photodiode and rhodes.in.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 15:40
L25	15	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and peripheral with logic and photodiode and rhodes.in.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 15:40
L26	132	CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 15:40
L27	79	L26 and (field adj oxide fox)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 15:40
L28	16	("4374700" "5319604" "5461425" "5471515" "5541402" "5576763" "5612799" "5614744" "5625210" "5705846" "5708263" "5739562" "5757045" "6023081" "6040593" "6160282").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 15:40
L29	82	"5614744" and oxide	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 15:40
L30	47	"5614744" and (insulator oxide dielectric) near gate	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 15:40
L31	13	cmos adj (image imager imaging) and (dual double) near3 (dielectric insulator insulating oxide insulated)	US-PGPUB; USPAT	OR	ON	2005/12/15 15:40

L32	15	cmos adj (image imager imaging) and (dual double) near3 (dielectric insulator insulating oxide insulated)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/12/15 15:40
L33	244	cmos and (DGO Dual adj Gate adj Oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 15:40
L34	12	(US-20020096733-\$).did. or (US-5625210-\$ or US-5841176-\$ or US-5933190-\$ or US-6204524-\$ or US-6326652-\$ or US-6333205-\$ or US-6376868-\$ or US-6445014-\$ or US-6617174-\$ or US-6740915-\$ or US-6835637-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/12/15 15:40
L35	1668	(438/57,87,275).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/15 15:40
S31	64	(DGO Dual adj Gate adj Oxide) and (image imager imaging)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 16:09

S32	36	(US-20020028550-\$ or US-20020172070-\$ or US-20020187413-\$ or US-20020195669-\$ or US-20030015735-\$ or US-20030137892-\$ or US-20030224724-\$ or US-20040018711-\$ or US-20040070581-\$ or US-20040081069-\$ or US-20040102424-\$ or US-20040100895-\$ or US-20040106625-\$ or US-20040127501-\$ or US-20040132264-\$ or US-20040186111-\$ or US-20040214387-\$ or US-20050012791-\$ or US-20050018471-\$ or US-20050112835-\$).did. or (US-6362049-\$ or US-6459113-\$ or US-6573613-\$ or US-6642543-\$ or US-6680722-\$ or US-6720221-\$ or US-6756271-\$ or US-6781915-\$ or US-6785157-\$ or US-6794709-\$ or US-6806521-\$ or US-6833308-\$ or US-6838344-\$ or US-6864920-\$ or US-6902256-\$).did. or (KR-2002034316-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/08/16 16:21
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